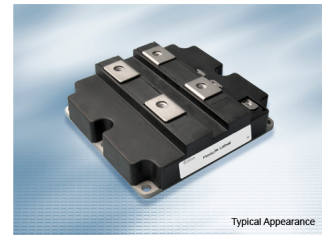


IHM-B module with Trench/Fieldstop IGBT4 and Emitter Controlled 4 diode

Features

- Electrical features
 - $V_{CES} = 3300\text{ V}$
 - $I_{C\text{nom}} = 825\text{ A} / I_{CRM} = 1650\text{ A}$
 - Low Q_g and C_{res}
 - High DC stability
 - High short-circuit capability
 - Low switching losses
 - Low V_{CESat}
 - $T_{vj\text{op}} = 150\text{ °C}$
 - Trench IGBT 4
 - Unbeatable robustness
 - V_{CESat} with positive temperature coefficient
 - High current density
- Mechanical features
 - ALSiC base plate for increased thermal cycling capability
 - High power density
 - Isolated base plate
 - Package with CTI > 600
 - RoHS compliant



Potential applications

- High power converters
- Medium voltage converters
- Motor drives
- Traction drives
- UPS systems
- Active frontend (energy recovery)
- Commercial Agriculture Vehicles

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

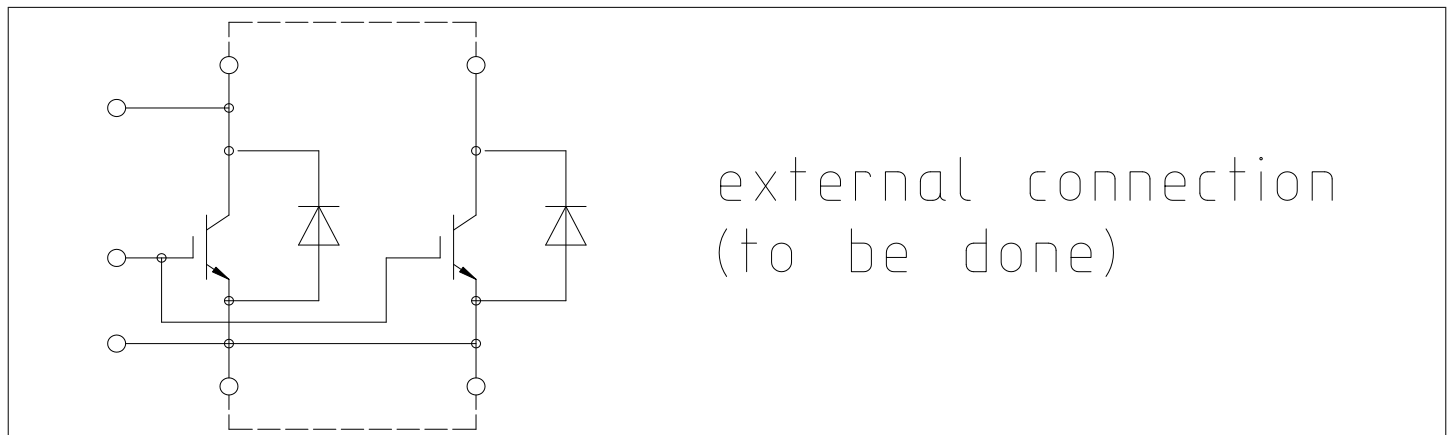


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50$ Hz	6.0	kV
Partial discharge extinction voltage	V_{isol}	RMS, $f = 50$ Hz, $Q_{PD} \leq 10$ pC	2.6	kV
DC stability	$V_{CE(D)}$	$T_{vj}=25^{\circ}\text{C}$, 100 Fit	2100	V
Material of module baseplate			AlSiC	
Creepage distance	d_{Creep}	terminal to heatsink	32.2	mm
Clearance	d_{Clear}	terminal to heatsink	19.1	mm
Comparative tracking index	CTI		> 600	

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Stray inductance module	L_{SCE}			9		nH	
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_C=25^{\circ}\text{C}$, per switch		0.12		m Ω	
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C=25^{\circ}\text{C}$, per switch		0.2		m Ω	
Storage temperature	T_{stg}		-40		150	$^{\circ}\text{C}$	
Mounting torque for modul mounting	M	- Mounting according to valid application note	M6, Screw	4.25		5.75	Nm
Terminal connection torque	M	- Mounting according to valid application note	M4, Screw	1.8		2.1	Nm
			M8, Screw	8		10	
Weight	G			800		g	

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Collector-emitter voltage	V_{CES}		$T_{vj} = -40^{\circ}\text{C}$	3300	V
			$T_{vj} = 150^{\circ}\text{C}$	3300	
Continous DC collector current	I_{CDC}	$T_{vj\ max} = 150^{\circ}\text{C}$	$T_C = 105^{\circ}\text{C}$	825	A
Repetitive peak collector current	I_{CRM}	$t_p = 1$ ms		1650	A
Gate-emitter peak voltage	V_{GES}			± 20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 825\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$	2.40	2.65	V
			$T_{vj} = 125\ ^\circ C$	3.00		
			$T_{vj} = 150\ ^\circ C$	3.13	3.28	
Gate threshold voltage	V_{GEth}	$I_C = 32\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$	5.20	5.80	6.40	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CE} = 1800\ V$		14		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$		1.5		Ω
Input capacitance	C_{ies}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		93.5		nF
Reverse transfer capacitance	C_{res}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		2.67		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 3300\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$		5	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$			400	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 825\ A, V_{CE} = 1800\ V, V_{GE} = \pm 15\ V, R_{Gon} = 0.5\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.560		μs
			$T_{vj} = 125\ ^\circ C$	0.605		
			$T_{vj} = 150\ ^\circ C$	0.615		
Rise time (inductive load)	t_r	$I_C = 825\ A, V_{CE} = 1800\ V, V_{GE} = \pm 15\ V, R_{Gon} = 0.5\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.130		μs
			$T_{vj} = 125\ ^\circ C$	0.150		
			$T_{vj} = 150\ ^\circ C$	0.160		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 825\ A, V_{CE} = 1800\ V, V_{GE} = \pm 15\ V, R_{Goff} = 7\ \Omega$	$T_{vj} = 25\ ^\circ C$	3.200		μs
			$T_{vj} = 125\ ^\circ C$	3.450		
			$T_{vj} = 150\ ^\circ C$	3.500		
Fall time (inductive load)	t_f	$I_C = 825\ A, V_{CE} = 1800\ V, V_{GE} = \pm 15\ V, R_{Goff} = 7\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.900		μs
			$T_{vj} = 125\ ^\circ C$	1.450		
			$T_{vj} = 150\ ^\circ C$	1.650		
Turn-on energy loss per pulse	E_{on}	$I_C = 825\ A, V_{CE} = 1800\ V, L_\sigma = 85\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 0.5\ \Omega, di/dt = 4700\ A/\mu s (T_{vj} = 150\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	920		mJ
			$T_{vj} = 125\ ^\circ C$	1450		
			$T_{vj} = 150\ ^\circ C$	1630		
Turn-off energy loss per pulse	E_{off}	$I_C = 825\ A, V_{CE} = 1800\ V, L_\sigma = 85\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 7\ \Omega, dv/dt = 1700\ V/\mu s (T_{vj} = 150\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	1100		mJ
			$T_{vj} = 125\ ^\circ C$	1470		
			$T_{vj} = 150\ ^\circ C$	1580		
SC data	I_{SC}	$V_{GE} \leq 15\ V, V_{CC} = 2400\ V, V_{CEmax} = V_{CES} - L_{sCE} * di/dt$	$t_P \leq 10\ \mu s, T_{vj} \leq 150\ ^\circ C$	3600		A
Thermal resistance, junction to case	R_{thJC}	per IGBT			18.0	K/kW

Table 4 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, case to heatsink	R_{thCH}	per IGBT, $\lambda_{grease} = 1 \text{ W/(m}^2\text{K)}$		7.17		K/kW
Temperature under switching conditions	T_{vjop}		-40		150	°C

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = -40 \text{ }^\circ\text{C}$	3300	V
			$T_{vj} = 150 \text{ }^\circ\text{C}$	3300	
Continuous DC forward current	I_F		825	A	
Repetitive peak forward current	I_{FRM}	$t_p = 1 \text{ ms}$	1650	A	
I^2t - value	I^2t	$t_p = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125 \text{ }^\circ\text{C}$	280	kA ² s
			$T_{vj} = 150 \text{ }^\circ\text{C}$	253	
Maximum power dissipation	P_{RQM}	$T_{vj} = 150 \text{ }^\circ\text{C}$	2400	kW	
Minimum turn-on time	t_{onmin}		10	µs	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Forward voltage	V_F	$I_F = 825 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		2.55	2.95	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$		2.30		
			$T_{vj} = 150 \text{ }^\circ\text{C}$		2.20	2.50	
Peak reverse recovery current	I_{RM}	$V_R = 1800 \text{ V}, I_F = 825 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 4700 \text{ A}/\mu\text{s} (T_{vj} = 150 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		1180		A
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1240		
			$T_{vj} = 150 \text{ }^\circ\text{C}$		1250		
Recovered charge	Q_r	$V_R = 1800 \text{ V}, I_F = 825 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 4700 \text{ A}/\mu\text{s} (T_{vj} = 150 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		430		µC
			$T_{vj} = 125 \text{ }^\circ\text{C}$		830		
			$T_{vj} = 150 \text{ }^\circ\text{C}$		970		
Reverse recovery energy	E_{rec}	$V_R = 1800 \text{ V}, I_F = 825 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 4700 \text{ A}/\mu\text{s} (T_{vj} = 150 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		390		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$		875		
			$T_{vj} = 150 \text{ }^\circ\text{C}$		1050		

Table 6 **Characteristic values (continued)**

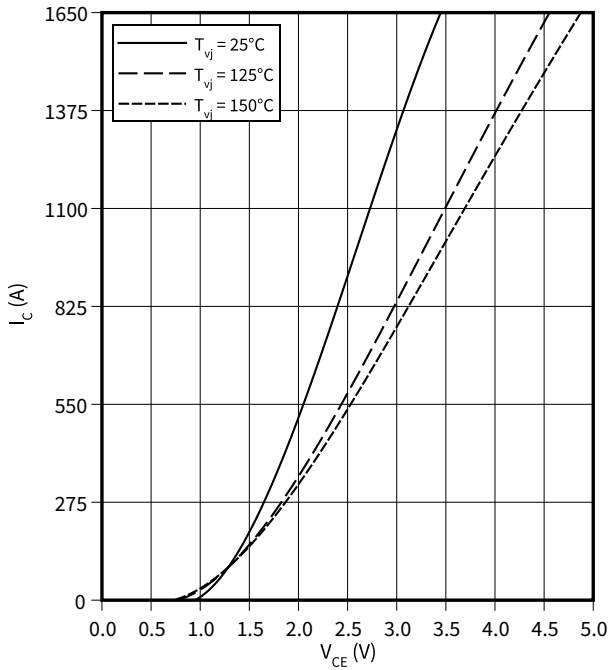
Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	R_{thJC}	per diode			25.2	K/kW
Thermal resistance, case to heatsink	R_{thCH}	per diode, $\lambda_{grease} = 1 \text{ W/(m}^2\text{K)}$		9.43		K/kW
Temperature under switching conditions	$T_{vj\ op}$		-40		150	°C

4 Characteristics diagrams

output characteristic (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

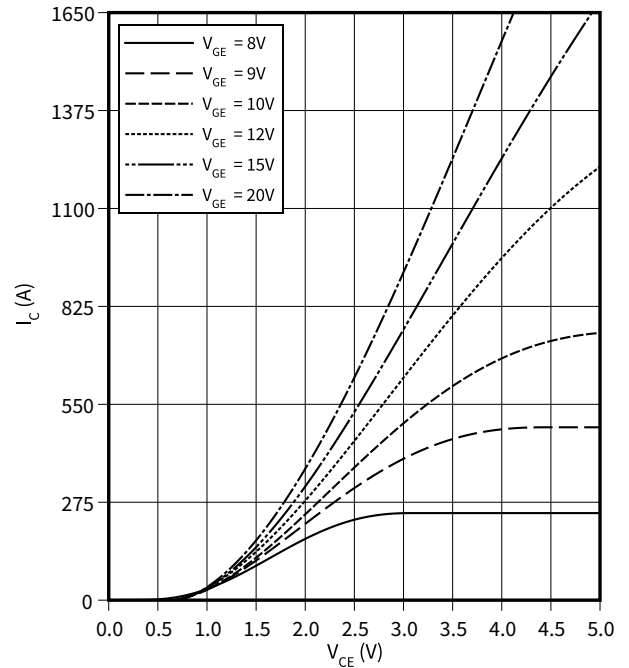
$$V_{GE} = 15 \text{ V}$$



output characteristic (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

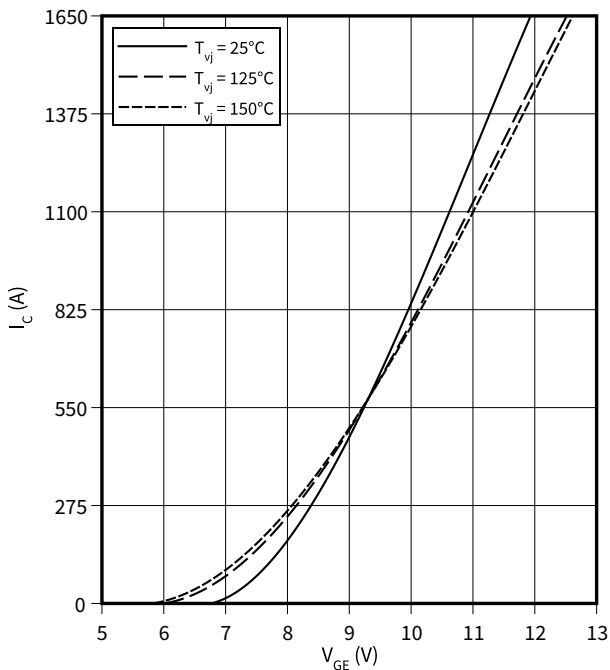
$$T_{vj} = 150 \text{ °C}$$



transfer characteristic (typical), IGBT, Inverter

$$I_C = f(V_{GE})$$

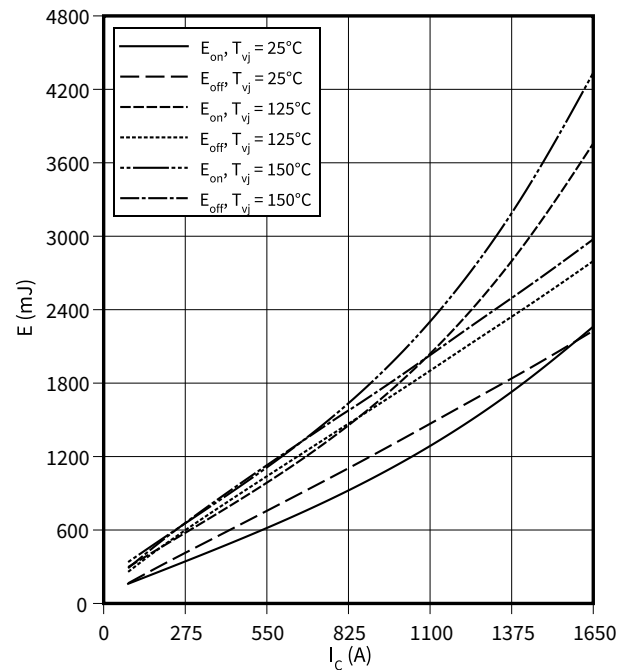
$$V_{CE} = 20 \text{ V}$$



switching losses (typical), IGBT, Inverter

$$E = f(I_C)$$

$$R_{Goff} = 7 \text{ } \Omega, R_{Gon} = 0.5 \text{ } \Omega, V_{CE} = 1800 \text{ V}, V_{GE} = \pm 15 \text{ V}$$

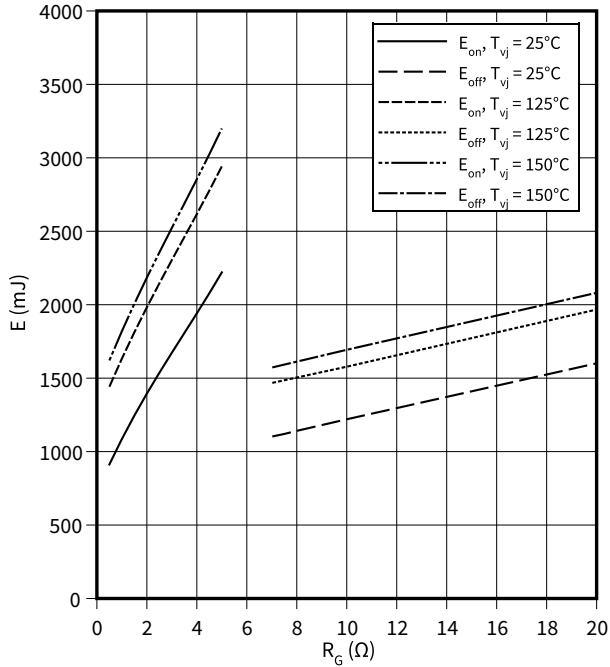


4 Characteristics diagrams

switching losses (typical), IGBT, Inverter

$E = f(R_G)$

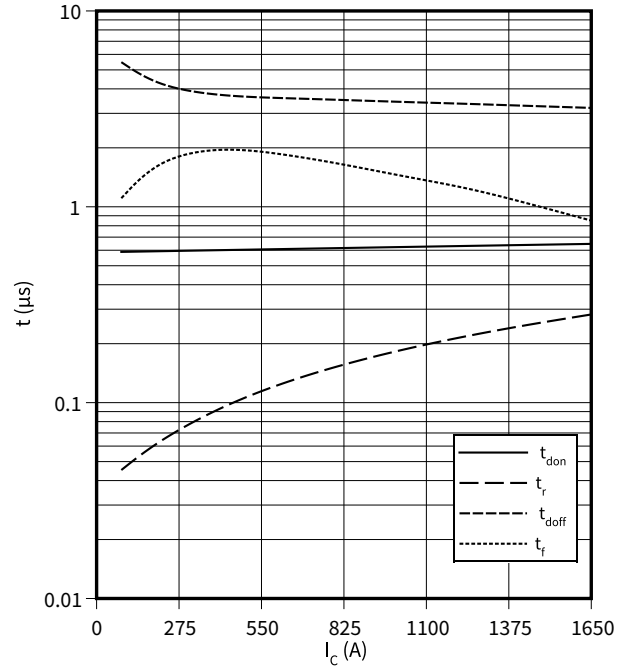
$I_C = 825 \text{ A}, V_{CE} = 1800 \text{ V}, V_{GE} = \pm 15 \text{ V}$



switching times (typical), IGBT, Inverter

$t = f(I_C)$

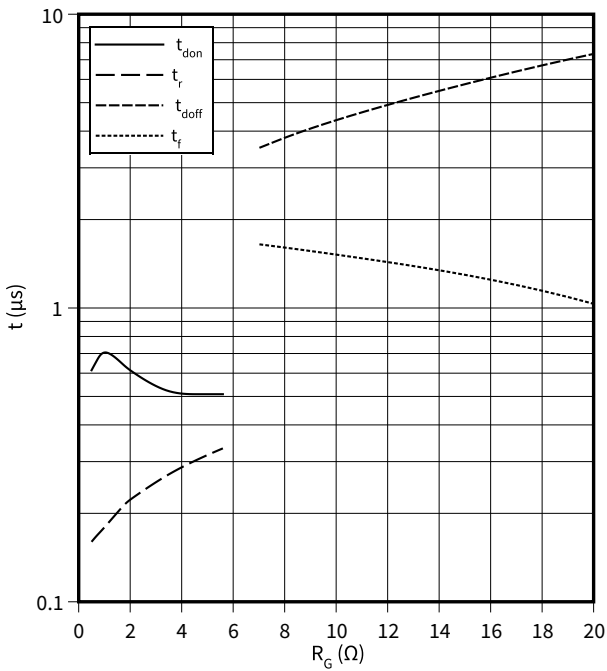
$R_{Goff} = 7 \Omega, R_{Gon} = 0.5 \Omega, V_{CE} = 1800 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 150 \text{ }^\circ\text{C}$



switching times (typical), IGBT, Inverter

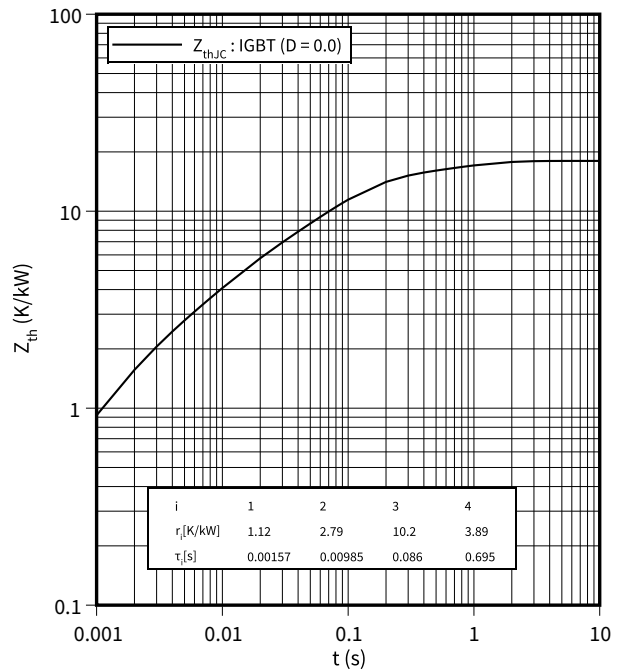
$t = f(R_G)$

$I_C = 825 \text{ A}, V_{CE} = 1800 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 150 \text{ }^\circ\text{C}$



transient thermal impedance, IGBT, Inverter

$Z_{th} = f(t)$

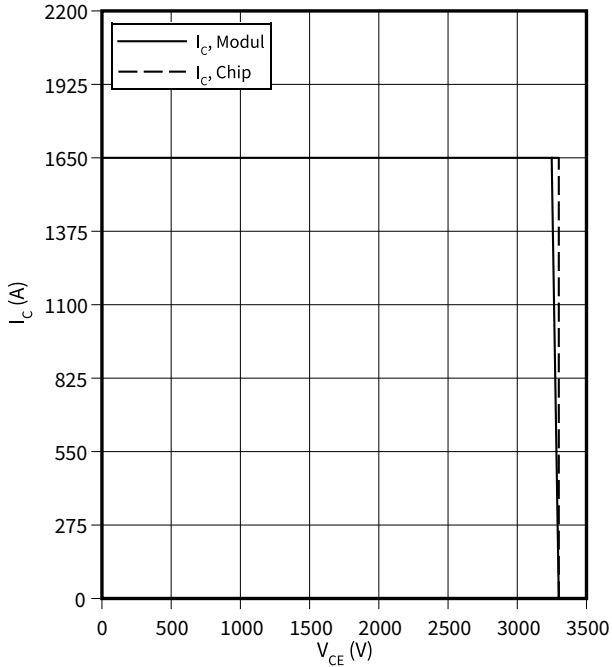


4 Characteristics diagrams

reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$

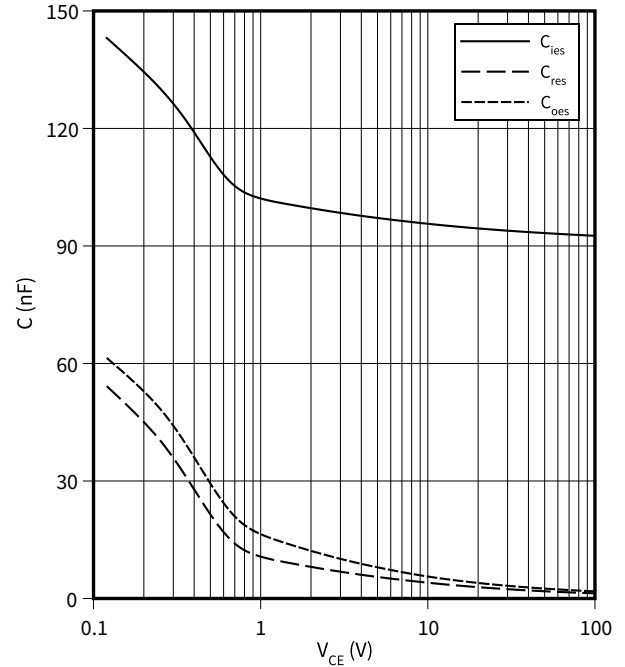
$R_{Goff} = 7 \Omega$, $V_{GE} = 15 V$, $T_{vj} = 150 \text{ }^\circ\text{C}$



capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$

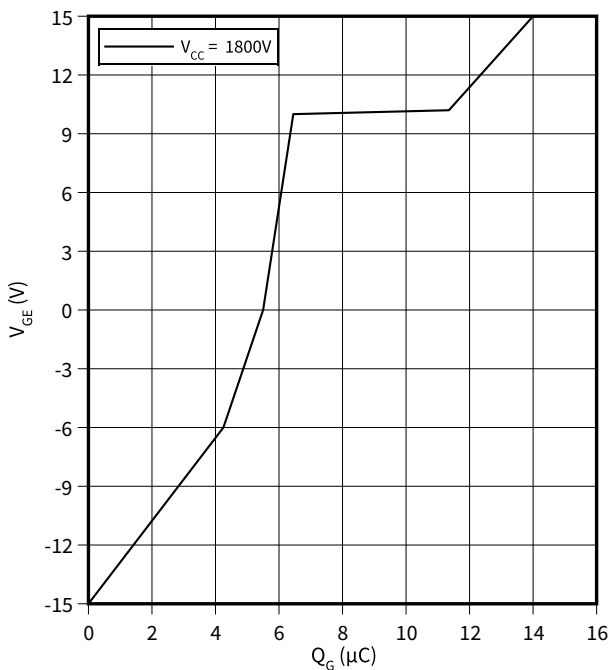
$f = 1000 \text{ kHz}$, $V_{GE} = 0 V$, $T_{vj} = 25 \text{ }^\circ\text{C}$



gate charge characteristic (typical), IGBT, Inverter

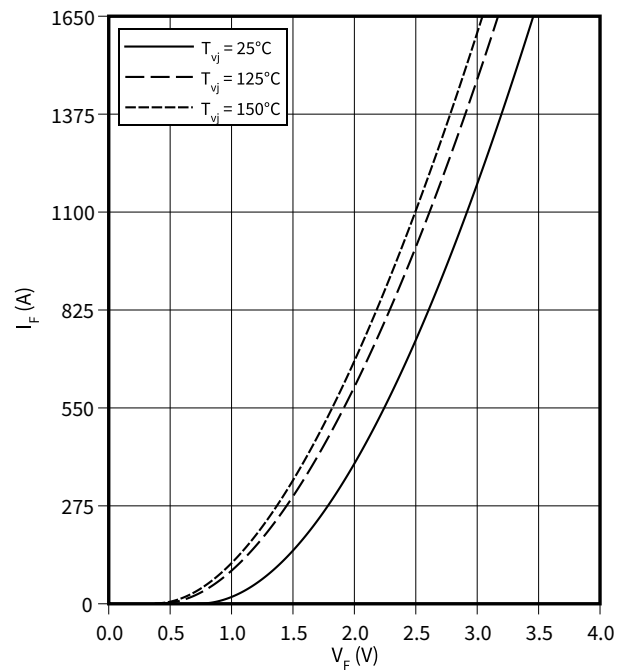
$V_{GE} = f(Q_G)$

$I_C = 825 A$, $T_{vj} = 25 \text{ }^\circ\text{C}$



forward characteristic of (typical), Diode, Inverter

$I_F = f(V_F)$

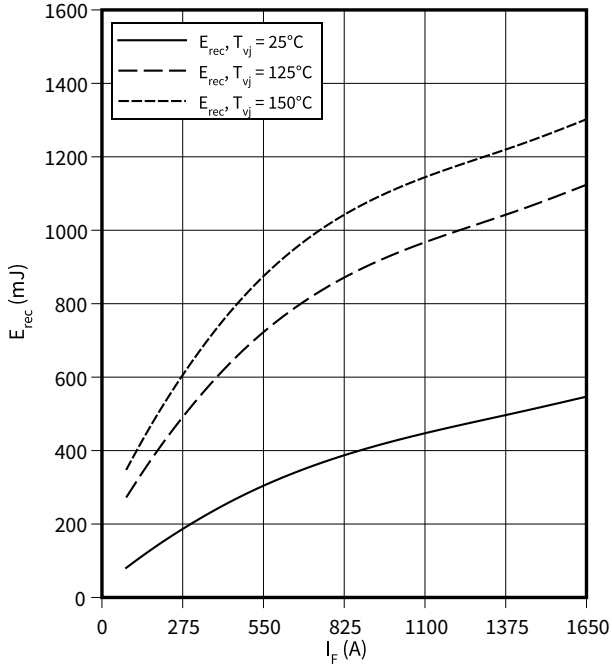


4 Characteristics diagrams

switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

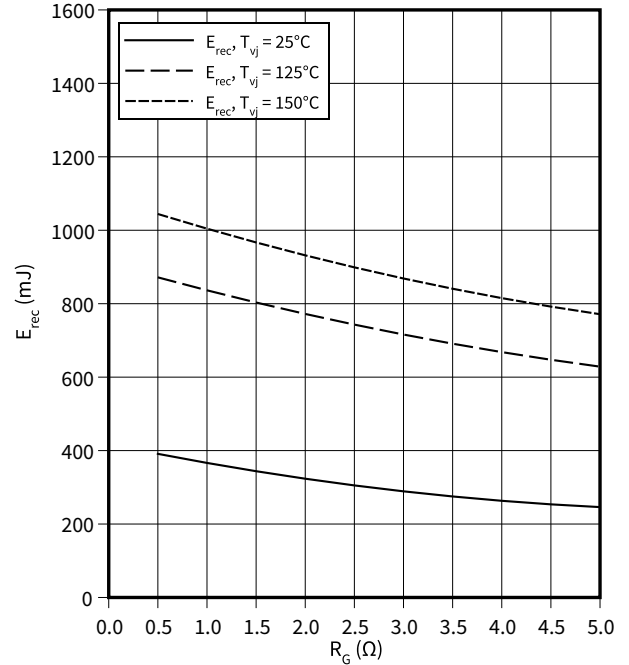
$V_{CE} = 1800\text{ V}, R_{Gon} = R_{Gon}(IGBT)$



switching losses (typical), Diode, Inverter

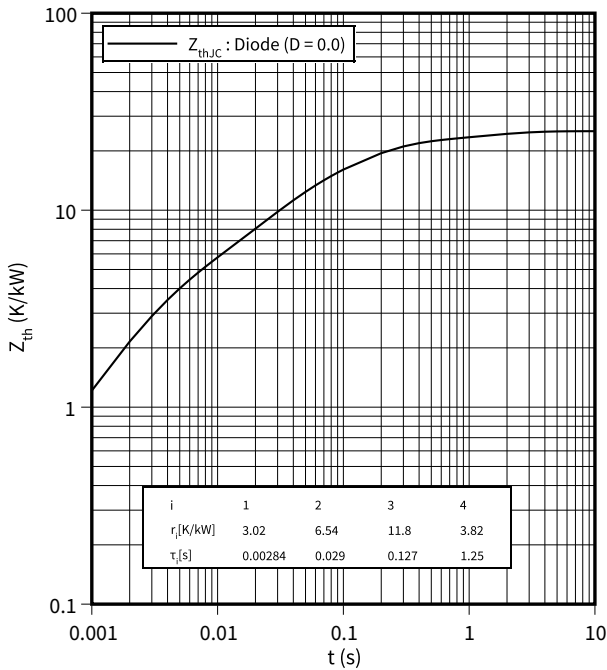
$E_{rec} = f(R_G)$

$V_{CE} = 1800\text{ V}, I_F = 825\text{ A}$



transient thermal impedance , Diode, Inverter

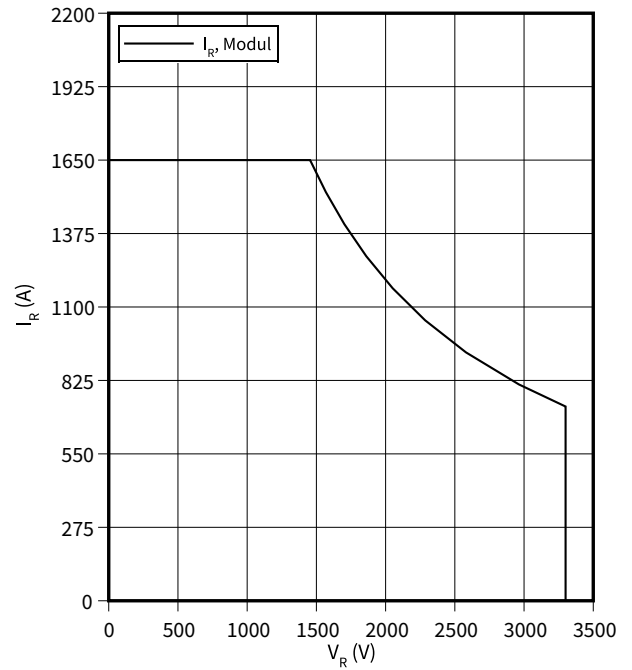
$Z_{th} = f(t)$



safe operation area (SOA), Diode, Inverter

$I_R = f(V_R)$

$T_{vj} = 150\text{ °C}$



5 Circuit diagram

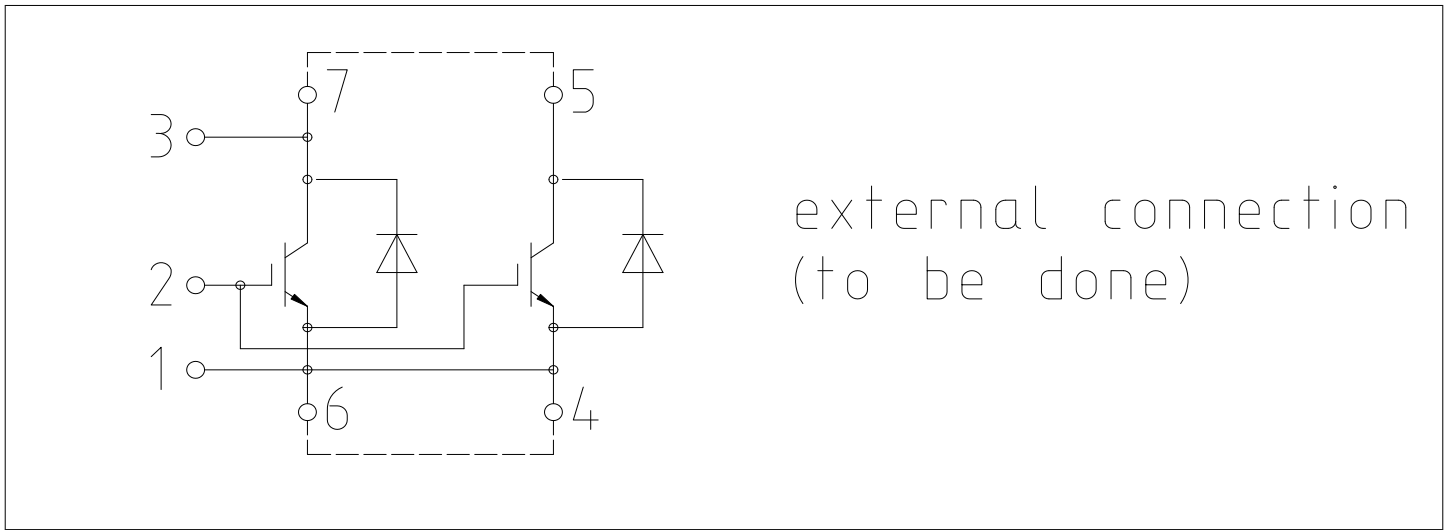


Figure 2

6 Package outlines

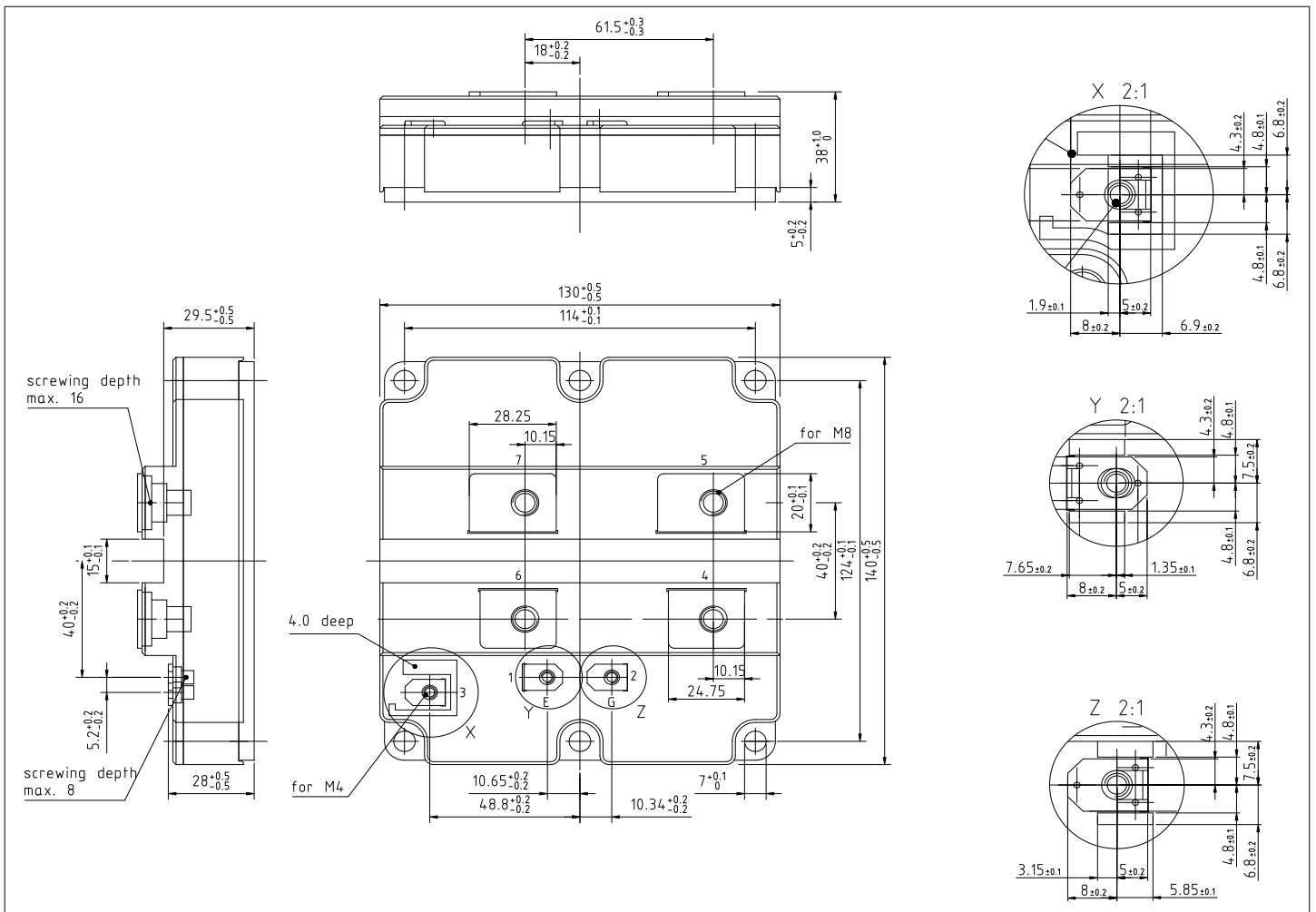


Figure 3

7 Module label code



Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 - 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 - 21	15
	Date code (production week)	22 - 23	30
Example	 		
	71549142846550549911530		71549142846550549911530

Figure 4

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